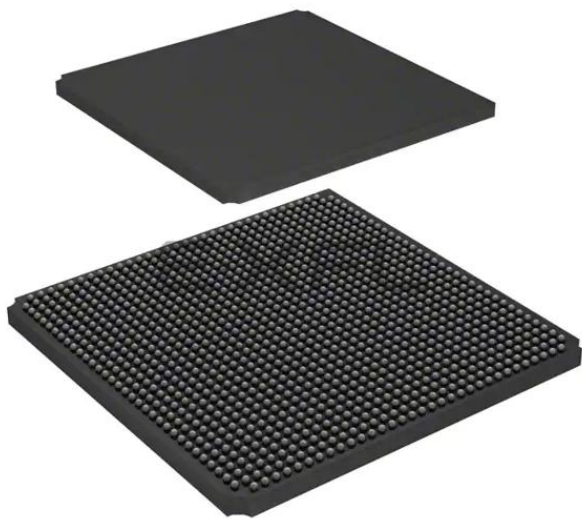




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	481000
Total RAM Bits	33792000
Number of I/O	584
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	1152-BBGA, FCBGA
Supplier Device Package	1152-FCBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf500tl-fcg1152e

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3 References

The following documents are recommended references. For more information about PolarFire static and dynamic power data, see the [PolarFire Power Estimator Spreadsheet](#).

- [PO0137](#): PolarFire FPGA Product Overview
- [ER0217](#): PolarFire FPGA Pre-Production Device Errata
- [UG0722](#): PolarFire FPGA Packaging and Pin Descriptions Users Guide
- [UG0726](#): PolarFire FPGA Board Design User Guide
- [UG0686](#): PolarFire FPGA User I/O User Guide
- [UG0680](#): PolarFire FPGA Fabric User Guide
- [UG0714](#): PolarFire FPGA Programming User Guide
- [UG0684](#): PolarFire FPGA Clocking Resources User Guide
- [UG0687](#): PolarFire FPGA 1G Ethernet Solutions User Guide
- [UG0727](#): PolarFire FPGA 10G Ethernet Solutions User Guide
- [UG0748](#): PolarFire FPGA Low Power User Guide
- [UG0676](#): PolarFire FPGA DDR Memory Controller User Guide
- [UG0743](#): PolarFire FPGA Debugging User Guide
- [UG0725](#): PolarFire FPGA Device Power-Up and Resets User Guide
- [UG0677](#): PolarFire FPGA Transceiver User Guide
- [UG0685](#): PolarFire FPGA PCI Express User Guide
- [UG0753](#): PolarFire FPGA Security User Guide
- [UG0752](#): PolarFire FPGA Power Estimator User Guide

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{IL} Min (V)	V _{IL} Max (V)	V _{IH} Min (V)	V _{IH} ¹ Max (V)
SSTL135I	1.283	1.35	1.418	-0.3	V _{REF} - 0.09	V _{REF} + 0.09	1.418
SSTL135II	1.283	1.35	1.418	-0.3	V _{REF} - 0.09	V _{REF} + 0.09	1.418
HSTL15I	1.425	1.5	1.575	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.575
HSTL15II	1.425	1.5	1.575	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.575
HSTL135I	1.283	1.35	1.418	-0.3	V _{REF} - 0.09	V _{REF} + 0.09	1.418
HSTL135II	1.283	1.35	1.418	-0.3	V _{REF} - 0.09	V _{REF} + 0.09	1.418
HSTL12I	1.14	1.2	1.26	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.26
HSTL12II	1.14	1.2	1.26	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.26
HSUL18I	1.71	1.8	1.89	-0.3	0.3 x V _{DDI}	0.7 x V _{DDI}	1.89
HSUL18II	1.71	1.8	1.89	-0.3	0.3 x V _{DDI}	0.7 x V _{DDI}	1.89
HSUL12I	1.14	1.2	1.26	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.26
POD12I	1.14	1.2	1.26	-0.3	V _{REF} - 0.08	V _{REF} + 0.08	1.26
POD12II	1.14	1.2	1.26	-0.3	V _{REF} - 0.08	V _{REF} + 0.08	1.26

1. GPIO V_{IH} max is 3.45 V with PCI clamp diode turned off regardless of mode, that is, over-voltage tolerant.

2. For external stub-series resistance. This resistance is on-die for GPIO.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

Table 17 • Complementary Differential DC Output Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} ^{1,3} Min (V)	I _{OL} ² Min (mA)	I _{OH} ² Min (mA)
SSTL25I	2.375	2.5	2.625		V _{TT} – 0.608	V _{TT} + 0.608	8.1	8.1
SSTL25II	2.375	2.5	2.625		V _{TT} – 0.810	V _{TT} + 0.810	16.2	16.2
SSTL18I	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603	6.7	6.7
SSTL18II	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603	13.4	13.4
SSTL15I ⁴	1.425	1.5	1.575		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL15II ⁴	1.425	1.5	1.575		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /34	(V _{DDI} – V _{OH})/34
SSTL135I ⁴	1.283	1.35	1.418		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL135II ⁴	1.283	1.35	1.418		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /34	(V _{DDI} – V _{OH})/34
HSTL15I	1.425	1.5	1.575		0.4	V _{DDI} – 0.4	8	8
HSTL15II	1.425	1.5	1.575		0.4	V _{DDI} – 0.4	16	16
HSTL135I ⁴	1.283	1.35	1.418		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /50	(V _{DDI} – V _{OH})/50
HSTL135II ⁴	1.283	1.35	1.418		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /25	(V _{DDI} – V _{OH})/25
HSTL12I ⁴	1.14	1.2	1.26		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /50	(V _{DDI} – V _{OH})/50
HSUL18I ⁴	1.71	1.8	1.89		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /55	(V _{DDI} – V _{OH})/55
HSUL18II ⁴	1.71	1.8	1.89		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /25	(V _{DDI} – V _{OH})/25
HSUL12I ⁴	1.14	1.2	1.26		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /40	(V _{DDI} – V _{OH})/40
POD12I ^{3,4}	1.14	1.2	1.26		0.5 × V _{DDI}		V _{OL} /48	(V _{DDI} – V _{OH})/48
POD12II ^{3,4}	1.14	1.2	1.26		0.5 × V _{DDI}		V _{OL} /34	(V _{DDI} – V _{OH})/34

1. V_{OH} is the single-ended high-output voltage.
2. The total DC sink/source current of all IOs within a lane is limited as follows:
 - a. HSIO lane: 120 mA per 12 IO buffers.
 - b. GPIO lane: 160 mA per 12 IO buffers
3. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).

6.3.4 HSIO On-Die Termination

The following tables lists the on-die termination calibration accuracy specifications for HSIO bank.

Table 18 • Single-Ended Thevenin Termination (Internal Parallel Thevenin Termination)

Min (%)	Typ	Max (%)	Unit	Condition
–40	50	20	Ω	V _{DDI} = 1.8 V/1.5 V/1.35 V/1.2 V
–40	75	20	Ω	V _{DDI} = 1.8 V
–40	150	20	Ω	V _{DDI} = 1.8 V
–20	20	20	Ω	V _{DDI} = 1.5 V/1.35 V
–20	30	20	Ω	V _{DDI} = 1.5 V/1.35 V
–20	40	20	Ω	V _{DDI} = 1.5 V/1.35 V
–20	60	20	Ω	V _{DDI} = 1.5 V/1.35 V
–20	120	20	Ω	V _{DDI} = 1.5 V/1.35 V

Parameter	Description	Min (%)	Typ	Max (%)	Unit	Condition
Single-ended termination to $V_{SS}^{4,5}$	Internal	-20	120	20	Ω	$V_{DDI} = 2.5\text{ V}/1.8\text{ V}/1.5\text{ V}/1.2\text{ V}$
	parallel termination to V_{SS}	-20	240	20	Ω	$V_{DDI} = 2.5\text{ V}/1.8\text{ V}/1.5\text{ V}/1.2\text{ V}$

1. Measured across P to N with 400 mV bias.
2. Thevenin impedance is calculated based on independent P and N as measured at 50% of V_{DDI} .
3. For 50 Ω /75 Ω /150 Ω cases, nearest supported values of 40 Ω /60 Ω /120 Ω are used.
4. Measured at 50% of V_{DDI} .
5. Supported terminations vary with the IO type regardless of V_{DDI} nominal voltage. Refer to Libero for available combinations.

Standard	Description	V_I^1	V_H^1	V_{ID}^2	V_{ICM}^2	$V_{MEAS}^{3,4}$	$V_{REF}^{1,5}$	Unit
HSUL18I	HSUL 1.8 V Class I	$V_{REF} -$ 0.54	$V_{REF} +$ 0.54			V_{REF}	0.90	V
HSUL18II	HSUL 1.8 V Class II	$V_{REF} -$ 0.54	$V_{REF} +$ 0.54			V_{REF}	0.90	V
HSUL12	HSUL 1.2 V	$V_{REF} -$.22	$V_{REF} +$.22			V_{REF}	0.60	V
POD12I	Pseudo open drain (POD) logic 1.2 V Class I	$V_{REF} -$.15	$V_{REF} +$.15			V_{REF}	0.84	V
POD12II	POD 1.2 V Class II	$V_{REF} -$.15	$V_{REF} +$.15			V_{REF}	0.84	V
LVDS33	Low-voltage differential signaling (LVDS) 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
LVDS25	LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
LVDS18	LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
RSDS33	RSDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
RSDS25	RSDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
RSDS18	RSDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS33	Mini-LVDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS25	Mini-LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS18	Mini-LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
SUBLVDS33	Sub-LVDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
SUBLVDS25	Sub-LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
SUBLVDS18	Sub-LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
PPDS33	Point-to-point differential signaling 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
PPDS25	PPDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
PPDS18	PPDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
SLVS33	Scalable low- voltage signaling 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.200	0		V

Figure 1 • Output Delay Measurement—Single-Ended Test Setup

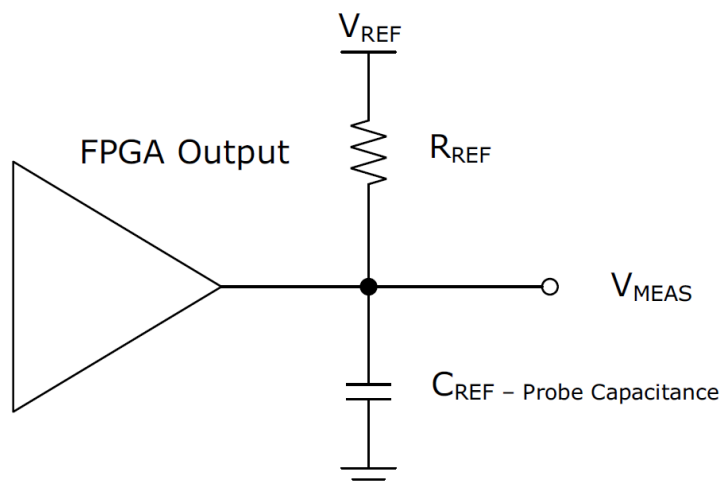
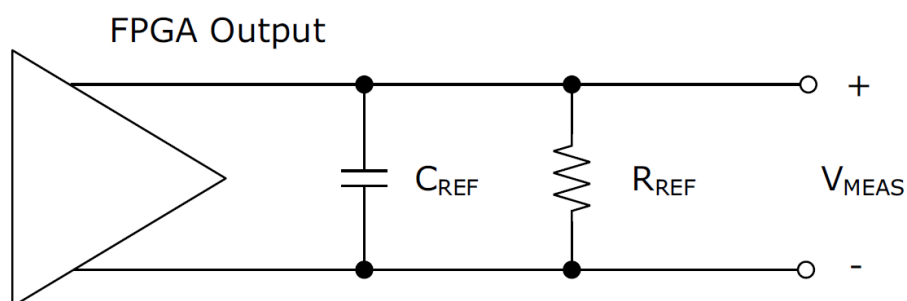


Figure 2 • Output Delay Measurement—Differential Test Setup



7.1.3 Input Buffer Speed

The following tables provide information about input buffer speed.

Table 24 • HSIO Maximum Input Buffer Speed

Standard	STD	-1	Unit
LVDS18	1250	1250	Mbps
RDS18	800	800	Mbps
MINILVDS18	800	800	Mbps
SUBLVDS18	800	800	Mbps
PPDS18	800	800	Mbps
SLVS18	800	800	Mbps
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Forwarded Clock-to-Data Skew
Output F _{MAX} 2:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F _{MAX} 4:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F _{MAX} 8:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
In delay, out delay, DLL delay step sizes			12.7	30	35	12.7	25	29.5	ps	

Table 34 • I/O CDR Switching Characteristics

Parameter	Min	Max	Unit
Data rate	266	1250	Mbps
Receiver Sinusoidal jitter tolerance ¹	0.2		UI

1. Jitter values based on bit error ratio (BER) of 10–12, 80 MHz sinusoidal jitter injected to Rx data.

Note: See the LVDS output buffer specifications for transmit characteristics.

7.2 Clocking Specifications

This section describes the PLL and DLL clocking and oscillator specifications.

7.2.1 Clocking

The following table provides clocking specifications.

Table 35 • Global and Regional Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Global clock F _{MAX}	F _{MAXG}	500	500	500	500	MHz	
Regional clock F _{MAX}	F _{MAXR}	375	375	375	375	MHz	Transceiver interfaces only
	F _{MAXR}	250	250	250	250	MHz	All other interfaces
Global clock duty cycle distortion	T _{DCDG}	190	190	190	190	ps	At 500 MHz

Parameter ¹	Symbol	Min	Typ	Max	Unit
Secondary output clock frequency ²	F _{OUTSF}	33.3		800	MHz
Input clock cycle-to-cycle jitter	F _{INJ}			200	ps
Output clock period cycle-to-cycle jitter (w/clean input)	T _{OUTJITTERP}			300	ps
Output clock-to-clock skew between two outputs with the same phase settings	T _{SKEW}			±200	ps
DLL lock time	T _{LOCK}	16		16K	Reference clock cycles
Minimum reset pulse width	T _{MRPW}	3			ns
Minimum input pulse width ³	T _{MIPW}	20			ns
Minimum input clock pulse width high	T _{MPWH}	400			ps
Minimum input clock pulse width low	T _{MPWL}	400			ps
Delay step size	T _{DEL}	12.7	30	35	ps
Maximum delay block delay ⁴	T _{DELMAX}	1.8		4.8	ns
Output clock duty cycle (with 50% duty cycle input) ⁵	T _{DUTY}	40		60	%
Output clock duty cycle (in phase reference mode) ⁵	T _{DUTY50}	45		55	%

1. For all DLL modes.
2. Secondary output clock divided by four option.
3. On load, direction, move, hold, and update input signals.
4. 128 delay taps in one delay block.
5. Without duty cycle correction enabled.

7.2.4

RC Oscillators

The following tables provide internal RC clock resources for user designs and additional information about designing systems with RF front end information about emitters generated on-chip to support programming operations.

Table 39 • 2 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC _{2FREQ}		2		MHz
Accuracy	RC _{2FACC}	−4		4	%
Duty cycle	RC _{2DC}	46		54	%
Peak-to-peak output period jitter	RC _{2PJIT}		5	10	ns
Peak-to-peak output cycle-to-cycle jitter	RC _{2CIIT}		5	10	ns
Operating current (V _{DD25})	RC _{2IVPPA}			60	μA
Operating current (V _{DD})	RC _{2IVDD}			2.6	μA

Table 40 • 160 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC _{SCFREQ}		160		MHz
Accuracy	RC _{SCFACC}	−4		4	%
Duty cycle	RC _{SCDC}	47		52	%
Peak-to-peak output period jitter	RC _{SCPJIT}			600	ps
Peak-to-peak output cycle-to-cycle jitter	RC _{SCCIIT}			172	ps
Operating current (V _{DD25})	RC _{SCVPPA}			599	μA

Parameter	Modes ¹	STD Min	STD Max	-1 Min	-1 Max	Unit
Transceiver RX_CLK range (non- deterministic PCS mode with global or regional fabric clocks)	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 4.8 Gbps		300		300	MHz
	20-bit, max data rate = 6.0 Gbps		300		300	MHz
	32-bit, max data rate = 10.3125 Gbps		325		325	MHz
	40-bit, max data rate = 10.3125 Gbps (-STD) / 12.7 Gbps (-1) ¹		260		320	MHz
	64-bit, max data rate = 10.3125 Gbps (-STD) / 12.7 Gbps (-1) ¹		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (-STD) / 12.7 Gbps (-1) ¹		130		160	MHz
	Fabric pipe mode 32-bit, max data rate = 6.0 Gbps		150		150	MHz
Transceiver TX_CLK range (deterministic PCS mode with regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 3.6 Gbps (-STD) / 4.25 Gbps (-1)		225		266	MHz
	20-bit, max data rate = 4.5 Gbps (-STD) / 5.32 Gbps (-1)		225		266	MHz
	32-bit, max data rate = 7.2 Gbps (-STD) / 8.5 Gbps (-1)		225		266	MHz
	40-bit, max data rate = 9.0 Gbps (-STD) / 10.6 Gbps (-1) ¹		225		266	MHz
	64-bit, max data rate = 10.3125 Gbps (-STD) / 12.7 Gbps (-1) ¹		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (-STD) / 12.7 Gbps (-1) ¹		130		160	MHz
Transceiver RX_CLK range (deterministic PCS mode with regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 3.6 Gbps (-STD) / 4.25 Gbps (-1)		225		266	MHz
	20-bit, max data rate = 4.5 Gbps (-STD) / 5.32 Gbps (-1)		225		266	MHz
	32-bit, max data rate = 7.2 Gbps (-STD) / 8.5 Gbps (-1)		225		266	MHz
	40-bit, max data rate = 9.0 Gbps (-STD) / 10.6 Gbps (-1) ¹		225		266	MHz
	64-bit, max data rate = 10.3125 Gbps (-STD) / 12.7 Gbps (-1) ¹		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (-STD) / 12.7 Gbps (-1) ¹		130		160	MHz

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions \(see page 6\)](#).

Note: Until specified, all modes are non-deterministic. For more information, see [UG0677: PolarFire FPGA Transceiver User Guide](#).

5. Improved jitter characteristics for a specific industry standard are possible in many cases due to improved reference clock or higher V_{CO} rate used.
6. Tx jitter is specified with all transmitters on the device enabled, a 10–12-bit error rate (BER) and Tx data pattern of PRBS7.
7. From the PMA mode, the TX_ELEC_IDLE port to the XVCR TXP/N pins.
FTxRefClk = 75 MHz with typical settings.
For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions](#) (see page 6). (see page 6)

7.4.6 Receiver Performance

The following table describes performance of the receiver.

Table 53 • PolarFire Transceiver Receiver Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Input voltage range	V_{IN}	0		$V_{DDA} + 0.3$	V	
Differential peak-to-peak amplitude	V_{IDPP}	140		1250	mV	
Differential termination	V_{ITERM}		85		Ω	
	V_{ITERM}		100		Ω	
	V_{ITERM}		150		Ω	
Common mode voltage	V_{ICMDC}^1	$0.7 \times V_{DDA}$		$0.9 \times V_{DDA}$	V	DC coupled
Exit electrical idle detection time	T_{EIDET}		50	100	ns	
Run length of consecutive identical digits (CID)	C_{ID}			200	UI	
CDR PPM tolerance ²	C_{DRPPM}			1.15	% UI	
CDR lock-to-data time	T_{LTD}				CDR_{REFCLK} UI	
CDR lock-to-ref time	T_{LTF}				CDR_{REFCLK} UI	
Loss-of-signal detect (Peak Detect Range setting = high) ⁹	$V_{DETLHIGH}$				mV	Setting = 1
	$V_{DETLHIGH}$				mV	Setting = 2
	$V_{DETLHIGH}$				mV	Setting = 3
	$V_{DETLHIGH}$				mV	Setting = 4
	$V_{DETLHIGH}$				mV	Setting = 5
	$V_{DETLHIGH}$				mV	Setting = 6
	$V_{DETLHIGH}$				mV	Setting = 7
Loss-of-signal detect (Peak Detect Range setting = low) ⁹	$V_{DETLLOW}$	65		175	mV	Setting = PCIe ^{3,7}
	$V_{DETLLOW}$	95		190	mV	Setting = SATA ^{4,8}
	$V_{DETLLOW}$	75		170	mV	Setting = 1
	$V_{DETLLOW}$	95		185	mV	Setting = 2
	$V_{DETLLOW}$	100		190	mV	Setting = 3
	$V_{DETLLOW}$	140		210	mV	Setting = 4
	$V_{DETLLOW}$	155		240	mV	Setting = 5
	$V_{DETLLOW}$	165		245	mV	Setting = 6
	$V_{DETLLOW}$	170		250	mV	Setting = 7
Sinusoidal jitter tolerance	T_{SJITOL}				UI	>8.5 Gbps – 12.7 Gbps ^{5, 10}

7.5.7 CPRI

The following table describes CPRI.

Table 66 • CPRI

	Data Rate	Min	Max	Unit
Total transmit jitter	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps ¹			UI
Receive jitter tolerance	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps ¹			UI

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions \(see page 6\)](#).

7.5.8 JESD204B

The following table describes JESD204B.

Table 67 • JESD204B

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	3.125 Gbps		0.35	UI
	6.25 Gbps		0.3	UI
	12.5 Gbps ¹			UI
Receive jitter tolerance	3.125 Gbps	0.56		UI
	6.25 Gbps	0.6		UI
	12.5 Gbps ¹			UI

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05V mode. See supply tolerance in the section [Recommended Operating Conditions \(see page 6\)](#).

7.6 Non-Volatile Characteristics

The following section describes non-volatile characteristics.

7.6.1 FPGA Programming Cycle and Retention

The following table describes FPGA programming cycle and retention.

Table 68 • FPGA Programming Cycles vs Retention Characteristics

Programming T _i	Programming Cycles, Max	Retention Years	Retention Years at T _i
0 °C to 85 °C	1000	20	85 °C
0 °C to 100 °C	500	20	100 °C
–20 °C to 100 °C	500	20	100 °C
–40 °C to 100 °C	500	20	100 °C
–40 °C to 85 °C	1000	16	100 °C
–40 °C to 55 °C	2000	12	100 °C

Note: Power supplied to the device must be valid during programming operations such as programming and verify . Programming recovery mode is available only for in-application programming mode and requires an external SPI flash.

7.6.2 FPGA Programming Time

The following tables describe FPGA programming time.

Table 69 • Master SPI Programming Time (IAP)

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T _{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS	17	25	s
		MPF300T, TL, TS, TLS	26	32	s
		MPF500T, TL, TS, TLS			s

Table 70 • Slave SPI Programming Time

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T _{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS	41 ¹		s
		MPF300T, TL, TS, TLS	50 ¹	60	s
		MPF500T, TL, TS, TLS			s

1. SmartFusion2 with MSS running at 100 MHz, MSS_SPI_0 port running at 6.67 MHz. Bitstream stored in DDR. DirectC version 4.1.

Table 71 • JTAG Programming Time

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T _{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS		56	s
		MPF300T, TL, TS, TLS ¹		95	s
		MPF500T, TL, TS, TLS			s

1. Programmer: FlashPro5 with TCK 10 MHz. PC Configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.

7.6.3 FPGA Bitstream Sizes

The following table describes FPGA bitstream sizes.

Table 72 • Initialization Client Sizes

Device	Plaintext	Ciphertext
MPF100T, TL, TS, TLS		
MPF200T, TL, TS, TLS	2916 KB	3006 KB
MPF300T, TL, TS, TLS	4265 KB	4403 KB
MPF500T, TL, TS, TLS		

Note: Worst case initializing all fabric LSRAM, USRAM, and UPROM.

Table 73 • Bitstream Sizes

File	Devices	FPGA	Security	SNVM (all pages)	FPGA+ SNVM	FPGA+ Sec	SNVM+ Sec	FPGA+ SNVM+ Sec
SPI	MPF100T, TL, TS, TLS							
DAT	MPF100T, TL, TS, TLS							
SPI	MPF200T, TL, TS, TLS	5.9 MB	3.4 KB	59.7 KB	5.9 MB	5.9 MB	62.2 KB	6.0 MB
DAT	MPF200T, TL, TS, TLS	5.9 MB	7.3 KB	61.2 KB	6.0 MB	5.9 MB	66.3 KB	6.0 MB
SPI	MPF300T, TL, TS, TLS	9.3 MB	3.5 KB	59.7 KB	9.6 MB	9.5 MB	62.2 KB	9.6 MB
DAT	MPF300T, TL, TS, TLS	9.3 MB	7.6 KB	61.2 KB	9.6 MB	9.5 MB	66.3 KB	9.6 MB
SPI	MPF500T, TL, TS, TLS							
DAT	MPF500T, TL, TS, TLS							

7.6.4 Digest Cycles

Digests verify the integrity of the programmed non-volatile data. Digests are a cryptographic hash of various data areas. Any digest that reports back an error raises the digest tamper flag.

Table 74 • Maximum Number of Digest Cycles

Retention Since Programmed (N = Number Digests During that Time) ¹										
Digest T _i	Storage and Operating T _i	N ≤300	N = 500	N = 1000	N = 1500	N = 2000	N = 4000	N = 6000	Unit	Retention
–40 to 100	–40 to 100	20 × LF	17 × LF	12 × LF	10 × LF	8 × LF	4 × LF	2 × LF	°C	Years
–40 to 100	0 to 100	20 × LF	17 × LF	12 × LF	10 × LF	8 × LF	4 × LF	2 × LF	°C	Years
–40 to 85	–40 to 85	20 × LF	20 × LF	20 × LF	20 × LF	16 × LF	8 × LF	4 × LF	°C	Years
–40 to 55	–40 to 55	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	°C	Years

1. LF = Lifetime factor as defined by the number of programming cycles the device has seen under the conditions listed in the following table.

Parameter	Typ	Max	Unit	Conditions
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ¹			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

7.6.7 Verify Time

The following tables describe verify time.

Table 81 • Standalone Fabric Verify Times

Parameter	Devices	Max	Unit
Standalone verification over JTAG	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	53 ¹	s
	MPF300T, TL, TS, TLS	90 ¹	s
	MPF500T, TL, TS, TLS		s
Standalone verification over SPI	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	37 ²	s
	MPF300T, TL, TS, TLS	55 ²	s
	MPF500T, TL, TS, TLS		s

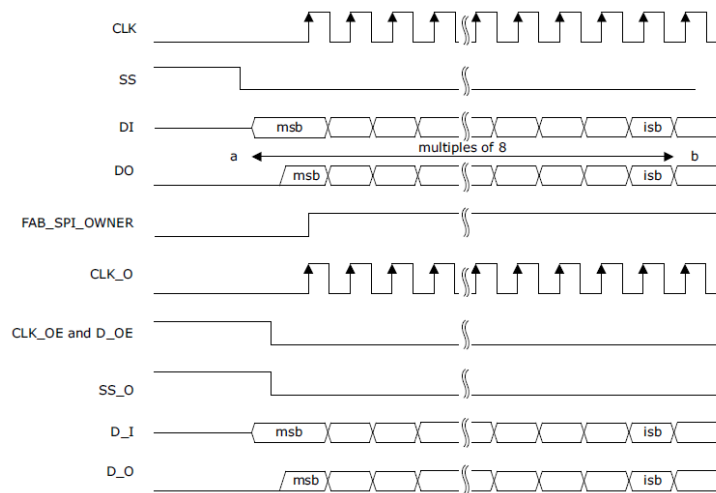
1. Programmer: FlashPro5, TCK 10 MHz; PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.
2. SmartFusion2 with MSS running at 100 MHz, MSS_SPI_0 port running at 6.67 MHz. DirectC version 4.1.

Notes:

- Standalone verify is limited to 2,000 total device hours over the industrial –40 °C to 100 °C temperature.
- Use the digest system service, for verify device time more than 2,000 hours.
- Standalone verify checks the programming margin on both the P and N gates of the push-pull cell.
- Digest checks only the P side of the push-pull gate. However, the push-pull gates work in tandem. Digest check is recommended if users believe they will exceed the 2,000-hour verify time specification.

Table 82 • Verify Time by Programming Hardware

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF100T, TL, TS, TLS						
MPF200T, TL, TS, TLS	9	67	53			s
MPF300T, TL, TS, TLS	14	95	90			s

Figure 4 • USPI Switching Characteristics

7.8.4 Tamper Detectors

The following section describes tamper detectors.

Table 91 • ADC Conversion Rate

Parameter	Description	Min	Typ ¹	Max
T _{CONV1}	Time from enable changing from zero to non-zero value to first conversion completes. Minimum value applies when POWEROFF = 0.	420 μs		470 μs
T _{CONVN}	Time between subsequent channel conversions.		480 μs	
T _{SETUP}	Data channel and output to valid asserted. Data is held until next conversion completes, that is >480 μs.	0 ns		
T _{VALID} ²	Width of the valid pulse.	1.625 μs		2 μs
T _{RATE}	Time from start of first set of conversions to the start of the next set. Can be considered as the conversion rate. Is set by the conversion rate parameter.	480 μs	Rate × 32 μs	8128 μs

1. Min, typ, and max refer to variation due to functional configuration and the raw TVS value. The actual internal correction time will vary based on the raw TVS value.
2. The pulse width varies depending on the time taken to complete the internal calibration multiplication, this can be up to 375 ns.

Note: Once the TVS block is active, the enable signal is sampled 25 ns before the falling edge of valid. The next enabled channel in the sequence 0-1-2-3 is started; that is, if channel 0 has just completed and only channels 0 and 3 are enabled, the next channel will be 3. When all the enabled channels in the sequence 0-1-2-3 are completed, the TVS waits for the conversion rate timer to expire. The enable signal may be changed at any time if it changes to 4'b0000 while valid is asserted (and 25 ns before valid is de-asserted), then no further conversions will be started.

Table 92 • Temperature and Voltage Sensor Electrical Characteristics

Parameter	Min	Typ	Max	Unit	Condition
Temperature sensing range	-40		125	°C	
Temperature sensing accuracy	-10		10	°C	

Table 107 • SPI Master Mode (PolarFire Master) During Device Initialization

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F _{MSCK}			40	MHz	

Table 108 • SPI Slave Mode (PolarFire Slave)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F _{SSCK}			80	MHz	

7.10.3 SmartDebug Probe Switching Characteristics

The following table describes characteristics of SmartDebug probe switching.

Table 109 • SmartDebug Probe Performance Characteristics

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V – 1	Unit
Maximum frequency of probe signal	F _{MAX}	100	100	100	100	MHz
Minimum delay of probe signal	T _{Min_delay}	13	12	13	12	ns
Maximum delay of probe signal	T _{Max_delay}	13	12	13	12	ns

7.10.4 DEVRST_N Switching Characteristics

The following table describes characteristics of DEVRST_N switching.

Table 110 • DEVRST_N Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
DEVRST_N ramp rate	DR _{RAMP}		10		μs	It must be a normal clean digital signal, with typical rise and fall times
DEVRST_N assert time	DR _{ASSERT}	1			μs	The minimum time for DEVRST_N assertion to be recognized
DEVRST_N de-assert time	DR _{DEASSERT}	2.75			ms	The minimum time DEVRST_N needs to be de-asserted before assertion

7.10.5 FF_EXIT Switching Characteristics

The following table describes characteristics of FF_EXIT switching.

Table 111 • FF_EXIT Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
FF_EXIT_N ramp rate	FF _{RAMP}		10		μs	
Minimum FF_EXIT_N assert time	FF _{ASSERT}	1			μs	The minimum time for FF_EXIT_N to be recognized
Minimum FF_EXIT_N de-assert time	FF _{DEASSERT}	170			μs	The minimum time FF_EXIT_N needs to be de-asserted before assertion

7.11 User Crypto

The following section describes user crypto.

7.11.1 TeraFire 5200B Switching Characteristics

The following table describes TeraFire 5200B switching characteristics.

Table 112 • TeraFire F5200B Switching Characteristics

Parameter	Symbol	VDD = 1.0 V STD	VDD = 1.0 V – 1	VDD = 1.05 V STD	VDD = 1.05 V – 1	Unit	Condition
Operating frequency	F _{MAX}	189		189		MHz	–40 °C to 100 °C

7.11.2 TeraFire 5200B Throughput Characteristics

The following tables for each algorithm describe the TeraFire 5200B throughput characteristics.

Note: Throughput cycle count collected with Athena TeraFire Core and RISCv running at 100 MHz.

Table 113 • AES

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-ECB-128 encrypt ¹	128	515	1095
	64K	50157	933
AES-ECB-128 decrypt ¹	128	557	1760
	64K	48385	1524
AES-ECB-256 encrypt ¹	128	531	1203
	64K	58349	1203
AES-ECB-256 decrypt ¹	128	589	1676
	64K	56673	1671
AES-CBC-256 encrypt ¹	128	576	1169
	64K	52547	1169
AES-CBC-256 decrypt ¹	128	585	1744
	64K	48565	1652
AES-GCM-128 encrypt ¹ , 128-bit tag, (full message encrypted/authenticated)	128	1925	2740
	64K	60070	2158
AES-GCM-256 encrypt ¹ , 128-bit tag, (full message encrypted/authenticated)	128	1973	2268
	64K	60102	2151

1. With DPA counter measures.

Table 114 • GMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-GCM-256 ¹ , 128-bit tag, (message is only authenticated)	128	1863	2211
	64K	49707	2128

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